

Program: SE

Curriculum Scheme: Revised 2016

Examination: Second Year Semester III

Course Code: ECC/320

Course Name: Electronics and devices circuit-I

Time: 1 hour

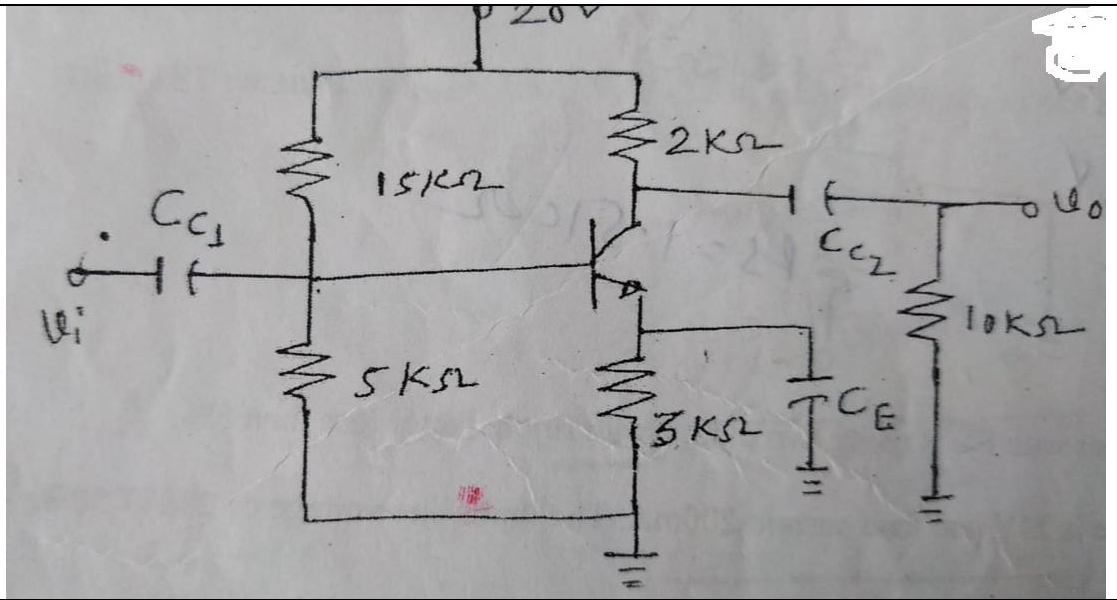
Max. Marks: 50

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Note to the students: - All the Questions are compulsory and carry equal marks.

Q1.	If the temperature of a diode increases, then leakage current and Base emitter voltage..... .
Option A:	Increases, Increases
Option B:	Decreases, decreases
Option C:	Decreases, Increases
Option D:	Increases, decreases
Q2.	Load Regulation should be _____ and Line Regulation should be _____ for good power Supply.
Option A:	as low as possible, as high possible
Option B:	as low as possible, as low possible
Option C:	as high as possible, as high possible
Option D:	as high as possible, as low possible
Q3.	If the a.c. input to a half-wave rectifier is an r.m.s value of $400/\sqrt{2}$ volts, then diode PIV rating is And efficiency is -----.
Option A:	400V, 40.6%
Option B:	$400/\sqrt{2}V$, 40.6%
Option C:	400V, 80.2%
Option D:	$400/\sqrt{2}V$, 80.2%
Q4.	The use of a capacitor filter in a rectifier circuit gives satisfactory performance only when the load Calculate ripple factor $f=50\text{Hz}$, $c=10\mu\text{f}$, $R_L=1\text{k}\Omega$
Option A:	current is high, 0.2886
Option B:	current is low, 0.2886
Option C:	current is high, 0.02886
Option D:	current is low, 0.02886
Q5.	Calculate I_B base current and I_c collector current $V_{cc}=9V$ $R_B = 330\text{k}\Omega$ $R_C = 1\text{k}\Omega$, $\beta = 100$ for fixed bias circuit.
Option A:	$25.15\mu\text{A}$, 2.5mA
Option B:	$2.5\mu\text{A}$, 2.5mA
Option C:	$25.15\mu\text{A}$, 25.15mA
Option D:	$2.6\mu\text{A}$, 26mA

Q6.	In JFET $I_{DSS}=7\text{mA}$, $V_p=-2.5\text{V}$, $V_{gs}=-1.2\text{V}$, find I_D drain current and g_{m0} .
Option A:	2.34mA,6.5ms
Option B:	1.89mA,5.6ms
Option C:	3.64mA,5.6ms
Option D:	0, infinite
Q7.	For a given circuit if CE capacitor is removed, what is an effect on voltage gain and input impedance.
Option A:	Voltage gain increases, Input impedance increases
Option B:	Voltage gain decreases, Input impedance increases
Option C:	Voltage gain increases, Input impedance decreases
Option D:	Voltage gain decreases, Input impedance decreases
Q8.	For a given Amplifier Calculate voltage gain, $I_{DSS}=7\text{mA}$, $V_p=-2.5\text{V}$ $V_{gs} = 1.6\text{V}$, $g_{m0}=5600\mu\text{s}$, $R_g=1\text{M}\Omega$, $R_d=2\text{K}\Omega$, $R_L=10\text{K}\Omega$
Option A:	-3.36
Option B:	4.032
Option C:	20.16
Option D:	5.06
Q9.	Calculate output resistance of an amplifier circuit. (use circuit of Q.8)
Option A:	10KΩ
Option B:	1.667KΩ
Option C:	2kΩ

Option D:	Infinite
Q10.	Select features of Common collector Amplifier. (more than one answer correct)
Option A:	used as an amplifier
Option B:	Output resistance low, Input resistance high
Option C:	Voltage gain =1
Option D:	Output resistance high, Input resistance low
Q11.	In CE amplifier RE bypassed if load resistor is given, Voltage gain is given by
Option A:	$\beta RC / r\pi$
Option B:	$-\beta(RC \parallel RL) / r\pi$
Option C:	$-\beta RC / r\pi$
Option D:	$-\beta RC / (r\pi \parallel RL)$
Q12.	Q point is affected by temperature. Temperature dependent parameters are
Option A:	β
Option B:	VBE
Option C:	ICBO, β
Option D:	VBE, ICBO, β
Q13.	BJT is current controlled device
Option A:	IC current depends on IB current
Option B:	IB current depends on IC current
Option C:	IC current depends on VBE voltage
Option D:	IB current depends on VBE voltage
Q14.	To use JFET as an amplifier, it should be biased in
Option A:	Saturation Region
Option B:	Ohmic region
Option C:	Linear region
Option D:	Cut off region
Q15.	For a given Amplifier, calculate voltage gain of an amplifier. $r\pi = 1.5K\Omega$, $\beta = 120$



Option A: 184.61

Option B: 800

Option C: 160

Option D: 190

Q16. For a circuit given in Q.15 calculate output resistance

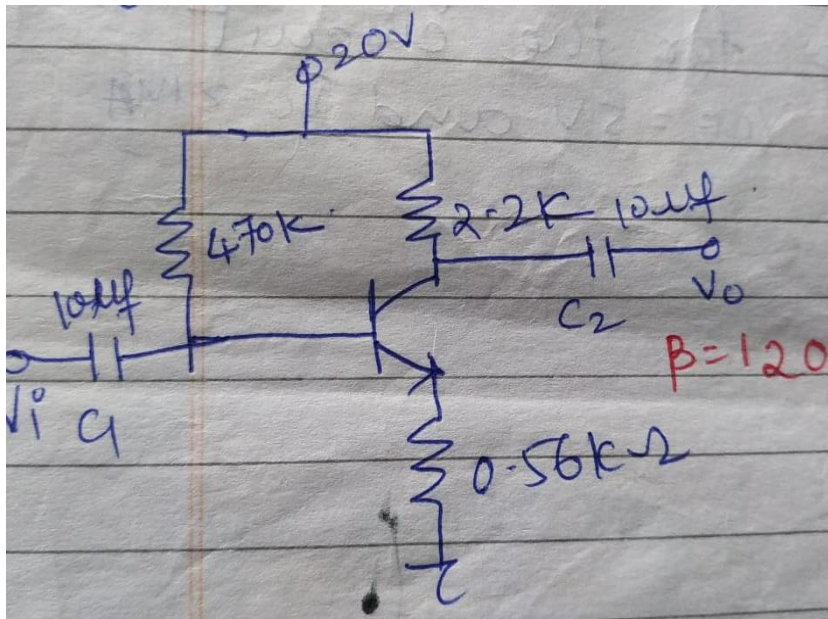
Option A: 2KΩ

Option B: 10KΩ

Option C: 1.96kΩ

Option D: Infinite

Q17. Calculate IB for a circuit shown



Option A: 33.125μA

Option B: 33.125mA

Option C:	6.625mA
Option D:	6.625 μ A
Q18.	Calculate stability factor for given specifications $V_{CC}=9V$ $R_B = 330K\Omega$ $R_C = 1K \Omega$, $\beta = 100$ for fixed bias circuit.
Option A:	1
Option B:	Infinite
Option C:	100
Option D:	101
Q19.	To pass audio signal through an Amplifier select a suitable corner frequency
Option A:	$F_H = 20Hz$, $F_L = 20KHZ$.
Option B:	$F_H = 200KHz$, $F_L = 2KHZ$.
Option C:	$F_H = 20kHz$, $F_L = 20HZ$.
Option D:	$F_H = \infty Hz$, $F_L = 0HZ$.
Q20.	Calculate lower cut-off frequency F_{LC3} if $C_3=1\mu f$ for a given circuit.
Option A:	0HZ
Option B:	1.3HZ
Option C:	3.1HZ
Option D:	∞ HZ
Q21.	Gain reduction in a low frequency region is due to _____.

Option A:	Coupling Capacitor
Option B:	Bypass Capacitor
Option C:	Coupling Capacitor and Bypass Capacitor
Option D:	Coupling Capacitor or Bypass Capacitor
Q22.	Which of the following condition is true for cut-off mode in transistor?
Option A:	The collector current is zero
Option B:	The collector current is proportional to the base current
Option C:	The base current is nonzero
Option D:	All the mentioned
Q23.	While designing voltage Amplifier using BJT which of the following biasing technique is used?
Option A:	Voltage divider bias
Option B:	Fixed bias
Option C:	Collector to base bias
Option D:	Self-bias
Q24.	Select the configuration from the following for $A_V = 100$, $R_i = 1\text{ M}\Omega$
Option A:	CE Amplifier
Option B:	CE Amplifier RE un bypassed
Option C:	CS Amplifier
Option D:	CB Amplifier
Q25.	Condition for Zero Temperature drift is
Option A:	$ V_P - V_{GS} = 0.63$
Option B:	$ V_P - V_{GS} = 0.36$
Option C:	$ V_{GS} - V_P = 0.63$
Option D:	$V_P - V_{GS} = 0.63$